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(54) **METHODS OF FORMING PLURALITIES OF CAPACITORS**

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(52) **U.S. Cl.** **438/239**; 438/243; 438/386;
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(57) **ABSTRACT**

(58) **Field of Classification Search** 438/238–396,
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See application file for complete search history.

A method of forming a plurality of capacitors includes providing a plurality of capacitor electrodes comprising sidewalls. The plurality of capacitor electrodes are supported at least in part with a retaining structure which engages the sidewalls, with the retaining structure comprising a fluid previous material. A capacitor dielectric material is deposited over the capacitor electrodes through the fluid previous material of the retaining structure effective to deposit capacitor dielectric material over portions of the sidewalls received below the retaining structure. Capacitor electrode material is deposited over the capacitor dielectric material through the fluid previous material of the retaining structure effective to deposit capacitor electrode material over at least some of the capacitor dielectric material received below the retaining structure. Integrated circuitry independent of method of fabrication is also contemplated.

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82 Claims, 11 Drawing Sheets

